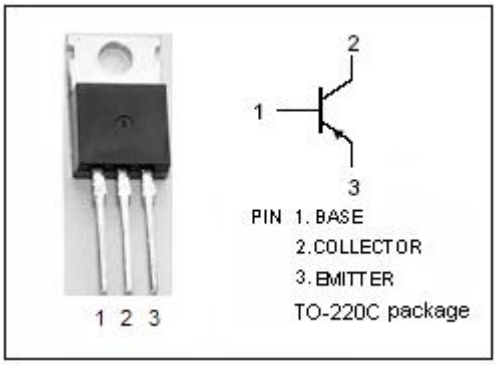
isc Silicon PNP Power Transistor 2N6134



DESCRIPTION

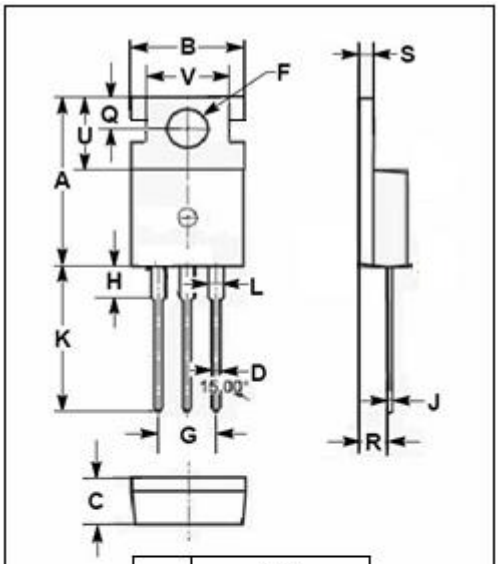
- DC Current Gain-
  : h_{FE} = 20-100@ I_C= -2.5A
- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= -80V(Min)
- Complement to Type 2N6131
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use in general-purpose amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-7	A
I_B	Base Current	-2	A
P_C	Collector Power Dissipation T_C=25℃	50	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -30mA; I_B= 0	-80		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -7A; I_B= -1.4A		-1.4	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -7A; V_{CE}= -4V		-3.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -80V; I_E= 0		-0.1	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= -80V; I_B= 0		-1.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0		-1.0	mA
h_{FE-1}	DC Current Gain	I_C= -2.5A ; V_{CE}= -4V	20	100	
h_{FE-2}	DC Current Gain	I_C= -7A ; V_{CE}= -4V	5		
f_T	Current-Gain—Bandwidth Product	I_C= -0.5A ; V_{CE}= -4V	2.5		MHz